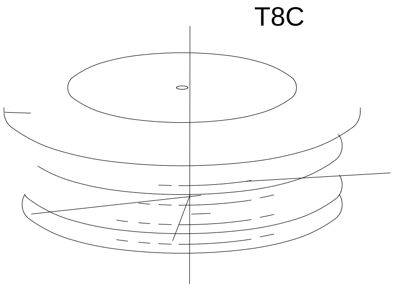
KP600-POWER THYRISTOR

6000-6600 V_{DRM}

FREE FLOATING TYPE THYRISTOR FOR PHASE CONTROL APPLICATIONS

Features:



ELECTRICAL CHARACTERISTICS AND RATINGS

Blocking - Off State

Device Type	V_{RRM} (1)	V_{DRM} (1)	V_{RSM} (1)
KP600/60	5100	5100	6000
KP600/62	5300	5300	6200
KP600/65	5600	5600	6500
KP600/66	5700	5700	6600

V_{RRM} = Repetitive peak reverse voltage
V_{DRM} = Repetitive peak off state voltage
V_{RSM} = Non repetitive peak reverse voltage (2)

Repetitive peak reverse leakage and off state leakage	I_{RRM}/I_{DRM}	2 mA 70 mA (3)
Critical rate of voltage rise	dv/dt (4)	1000 V/ s

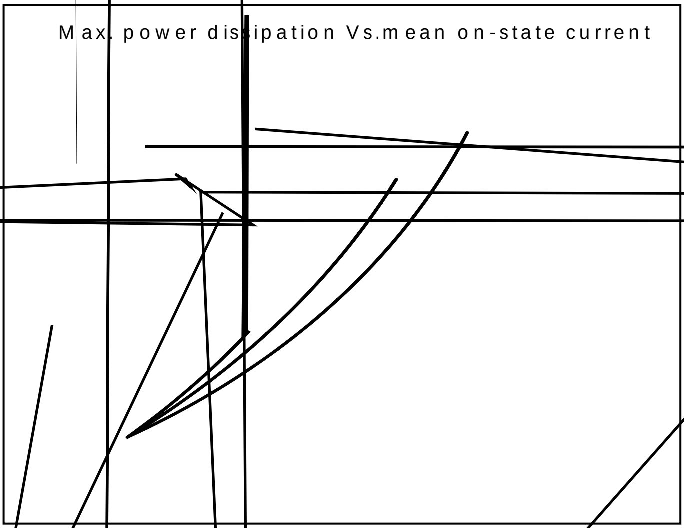
Conducting - On State

Gating

Parameter	Symbol	Min.	Max.	Typ.	Units	Conditions
Peak gate power dissipation	P_{GM}		20		W	
Average gate power dissipation	$P_{G(AV)}$		4		W	
Gate-trigger current	I_{GT}		200		mA	V_D =12 V;R_L = 3 ohms;T_j = +25 ºC
Gate- trigger voltage	V_{GT}	0.7	2.6		V	V_D = 12 V;R_L = 3 ohms;T_j = +25 ºC
Peak negative voltage	V_{GRM}		10		V	

Dynamic

Parameter	Symbol	Min.	Max.	Typ.	Units	Conditions
Delay time	t_d			3.0		



Max. power dissipation Vs.mean on-state current

CASE OUTLINE AND DIMENSIONS